

The SG – 269 photointerrupter high – performance standard type, combines high – output GaAs IRED with high sensitive phototransistor.

FEATURES

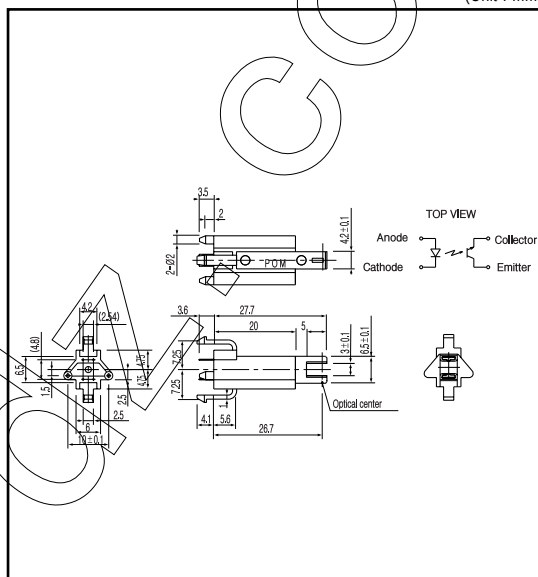
- PWB direct mount type
- GAP : 3.0mm
- Snap-in mount
- With the installation positioning boss
- Optical axis height from the mounting surface : 26.7mm

APPLICATIONS

- VTR
- Cassette mecha

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item		Symbol	Rating	Unit
Input	Power dissipation	P_D	75	mW
	Forward current	I_F	50	mA
	Reverse voltage	V_R	5	V
	Pulse forward current ¹⁾	I_{FP}	0.5	A
Output	Collector power dissipation	P_C	75	mW
	Collector current	I_C	20	mA
	C - E voltage	V_{CEO}	30	V
	E - C voltage	V_{ECO}	5	V
Operating temp. ²⁾		T_{opr}	-20 ~ +85	
Storage temp. ²⁾		T_{stg}	-30 ~ +100	
Soldering temp. ³⁾		T_{sol}	260	

*1. pulse width : t_w 100 μ sec. period : $T=10$ msec.

*2. No icebound or dew

*3. For MAX.5 seconds at the position of 1mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25)

Item		Symbol	Conditions	Min.	Typ.	Max.	Unit.
Input	Forward Voltage	V_F	$I_F = 20\text{mA}$		1.2	1.4	V
	Reverse current	I_R	$V_R = 5\text{V}$			10	μA
	Peak wavelength	λ_p	$I_F = 20\text{mA}$		940		nm
Output	Collector dark current	I_{CEO}	$V_{CE} = 10\text{V}$		1	100	nA
	Light current	I_C	$I_F = 20\text{mA}$, $V_E = 5\text{V}$, Non-shading	0.2		5	mA
Transmissi	leakage current	$I_{C(OD)}$	$I_F = 20\text{mA}$, $V_E = 5\text{V}$ (shading)			10	μA
	CE saturation voltage	$V_{CE(Sat)}$	$I_F = 20\text{mA}$, $I_C = 0.1\text{mA}$		0.15	0.4	V
	Rise time	t_r	$V_{CC} = 5\text{V}$, $I_C = 0.1\text{mA}$, $R = 100\Omega$		50		$\mu\text{sec.}$
	Fall time	t_f			50		$\mu\text{sec.}$

